

**IN THE CLAIMS:**

**Amendments to the Claims**

Please amend claims 67-72 as shown below.

**Listing of Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-66 (canceled)

67. (currently amended) A plasma etching apparatus comprising:  
a vacuum chamber;  
vacuum generating means;  
a sample stage installed in the vacuum chamber for holding a sample thereon;  
a planar plate disposed in parallel with the sample stage in the vacuum chamber;  
means for generating plasma in a space between the sample stage and the planar plate;  
~~including electromagnetic wave supply means and magnetic field generating means;~~  
wherein said means for generating plasma includes:  
a first power source for applying a bias which supplies a first electromagnetic wave of UHF to the planar plate;  
a second power source which supplies a second electromagnetic wave for controlling a radical in the plasma to the planar plate;  
means for adjusting an output of the second power source;

a filter which supplies a superposed electromagnetic wave of the first and second electromagnetic waves;

a first tuner arranged between the first power source and the filter;

a second tuner arranged between the second power source and the filter;

magnetic field generating means;

a second~~third~~ power source for applying a bias to the sample stage;

gas supply means for supplying a source material gas into the plasma generated in the vacuum chamber;

wherein the planar plate includes a plurality of holes, and the source material gas is supplied through the plurality of holes; and

wherein a distance between the planar plate and the sample held on the sample stage is in a range from 30 mm to one half of the smaller of one of a diameter of the sample and a diameter of the planar plate.

68. (currently amended) A plasma etching apparatus according to claim 67, further comprising a ring-shaped member disposed at a periphery of the sample stage, wherein the ~~second~~~~third~~ power source is connected to the ring-shaped member.

69. (currently amended) A plasma etching apparatus according to claim 67, further comprising means for control of temperature of ~~the-a~~ ring-shaped member.

70. (currently amended) A plasma etching apparatus according to claim 67, wherein the ~~electromagnetic wave supply means to generate the plasma~~ means for generating plasma provides an electromagnetic wave having a frequency ranging from 300 MHz to 500 MHz.

71. (currently amended) A plasma etching apparatus according to claim 67, ~~wherein the~~ further comprising a ring-shaped member which includes a surface to be brought into contact with the plasma, the surface being made of one of silicon, carbon, silicon carbide, quartz, aluminum oxide, and aluminum.

72. (currently amended) A plasma etching apparatus according to claim 68, further comprising means for dividing a power from the ~~second~~ third power source, the dividing means being configured so as to divide high frequency power from the ~~second~~ third power source into one part for the sample stage and another part for the ring-shaped member.